

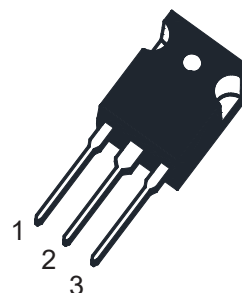
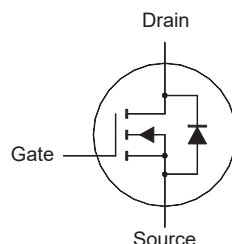
N-Channel Enhancement Mode MOSFET

Features

- Low $R_{DS(on)}$
- Low Miller Capacitance
- Fully Characterized Capacitance and Avalanche
- Halogen and Antimony Free(HAF), RoHS compliant

Application

- BLDC Motor drive applications
- Battery powered circuits
- Synchronous rectifier applications
- Resonant mode power supplies



TO-247 Plastic Package
1.Gate 2.Drain 3.Source

Key Parameters

Parameter	Value	Unit
BV_{DSS}	100	V
$R_{DS(on)}$ Max	4.8 @ $V_{GS} = 10$ V	m Ω
	6.3 @ $V_{GS} = 4.5$ V	
$V_{GS(th)}$ typ	1.9	V
Q_g typ	78 @ $V_{GS} = 10$ V	nC

Absolute Maximum Ratings (at $T_a = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	108	A
		68	
Peak Drain Current, Pulsed ¹⁾	I_{DM}	480	A
Avalanche Current	I_{AS}	30	A
Single Pulse Avalanche Energy ²⁾	E_{AS}	226.5	mJ
Power Dissipation	P_D	104.1	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Case	$R_{\theta JC}$	1.2	$^\circ\text{C/W}$
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	40	$^\circ\text{C/W}$

¹⁾ Pulse Test: Pulse Width ≤ 100 μs , Duty Cycle $\leq 2\%$, Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)} = 150^\circ\text{C}$.

²⁾ Limited by $T_{J(MAX)}$, starting $T_J = 25^\circ\text{C}$, $L = 0.5$ mH, $R_g = 25$ Ω , $I_{AS} = 30$ A, $V_{GS} = 10$ V.

Characteristics at $T_a = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit
STATIC PARAMETERS					
Drain-Source Breakdown Voltage at $I_D = 1\text{ mA}$	BV_{DSS}	100	-	-	V
Drain-Source Leakage Current at $V_{DS} = 100\text{ V}$	I_{DSS}	-	-	1	μA
Gate Leakage Current at $V_{GS} = \pm 20\text{ V}$	I_{GSS}	-	-	± 100	nA
Gate-Source Threshold Voltage at $V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	$V_{GS(th)}$	1.2	-	2.4	V
Drain-Source On-State Resistance at $V_{GS} = 10\text{ V}$, $I_D = 50\text{ A}$ at $V_{GS} = 4.5\text{ V}$, $I_D = 20\text{ A}$	$R_{DS(on)}$	- -	4.2 -	4.8 6.3	m Ω
DYNAMIC PARAMETERS					
Forward Transconductance at $V_{DS} = 5\text{ V}$, $I_D = 30\text{ A}$	g_{fs}	-	66.8	-	S
Gate Resistance at $V_{GS} = 0\text{ V}$, $V_{DS} = 0\text{ V}$, $f = 1\text{ MHz}$	R_g	-	1.1	-	Ω
Input Capacitance at $V_{GS} = 0\text{ V}$, $V_{DS} = 50\text{ V}$, $f = 1\text{ MHz}$	C_{iss}	-	3796	-	pF
Output Capacitance at $V_{GS} = 0\text{ V}$, $V_{DS} = 50\text{ V}$, $f = 1\text{ MHz}$	C_{oss}	-	683	-	pF
Reverse Transfer Capacitance at $V_{GS} = 0\text{ V}$, $V_{DS} = 50\text{ V}$, $f = 1\text{ MHz}$	C_{rss}	-	34	-	pF
Gate charge total at $V_{DS} = 50\text{ V}$, $I_D = 50\text{ A}$, $V_{GS} = 10\text{ V}$ at $V_{DS} = 50\text{ V}$, $I_D = 50\text{ A}$, $V_{GS} = 4.5\text{ V}$	Q_g	- -	78 42	- -	nC
Gate to Source Charge at $V_{DS} = 50\text{ V}$, $I_D = 50\text{ A}$, $V_{GS} = 10\text{ V}$	Q_{gs}	-	14	-	nC
Gate to Drain Charge at $V_{DS} = 50\text{ V}$, $I_D = 50\text{ A}$, $V_{GS} = 10\text{ V}$	Q_{gd}	-	24	-	nC
Turn-On Delay Time at $V_{DS} = 50\text{ V}$, $I_D = 50\text{ A}$, $V_{GS} = 10\text{ V}$, $R_g = 3.3\text{ }\Omega$	$t_{d(on)}$	-	27	-	ns
Turn-On Rise Time at $V_{DS} = 50\text{ V}$, $I_D = 50\text{ A}$, $V_{GS} = 10\text{ V}$, $R_g = 3.3\text{ }\Omega$	t_r	-	42	-	ns
Turn-Off Delay Time at $V_{DS} = 50\text{ V}$, $I_D = 50\text{ A}$, $V_{GS} = 10\text{ V}$, $R_g = 3.3\text{ }\Omega$	$t_{d(off)}$	-	26	-	ns
Turn-Off Fall Time at $V_{DS} = 50\text{ V}$, $I_D = 50\text{ A}$, $V_{GS} = 10\text{ V}$, $R_g = 3.3\text{ }\Omega$	t_f	-	6	-	ns
Body-Diode PARAMETERS					
Drain-Source Diode Forward Voltage at $I_S = 1\text{ A}$, $V_{GS} = 0\text{ V}$	V_{SD}	-	-	1.3	V
Body-Diode Continuous Current	I_S	-	-	108	A
Body-Diode Continuous Current, Pulsed	I_{SM}	-	-	480	A
Body Diode Reverse Recovery Time at $I_S = 50\text{ A}$, $V_{DD} = 50\text{ V}$, $di/dt = 200\text{ A}/\mu\text{s}$	t_{rr}	-	49	-	ns
Body Diode Reverse Recovery Charge at $I_S = 50\text{ A}$, $V_{DD} = 50\text{ V}$, $di/dt = 200\text{ A}/\mu\text{s}$	Q_{rr}	-	131	-	nC

Electrical Characteristics Curves

Fig. 1 Typical Output Characteristics

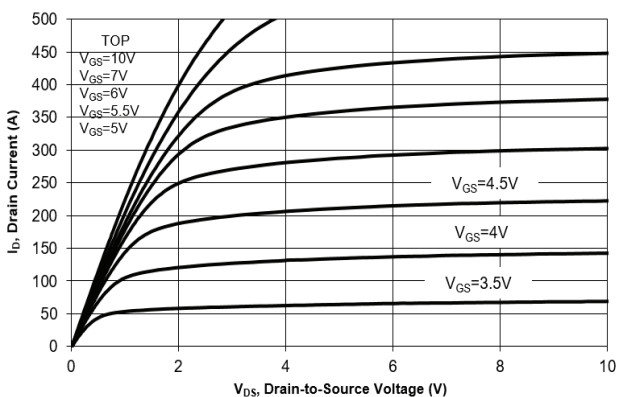


Fig. 2 Typical Transfer Characteristics

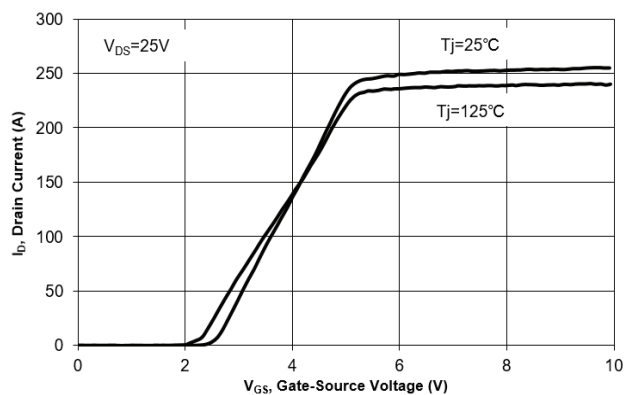


Fig. 3 On-Resistance vs. Drain Current

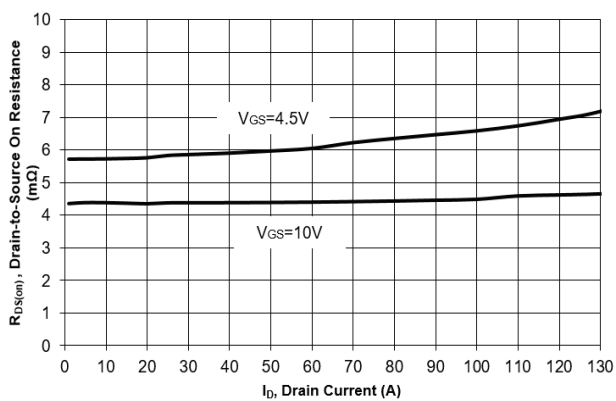


Fig. 4 On-Resistance vs. Gate to Source Voltage

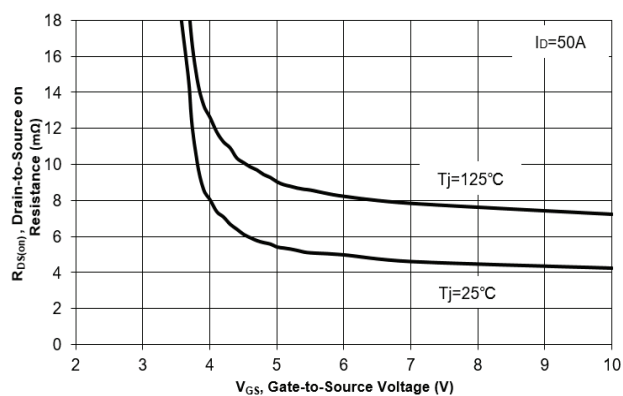


Fig. 5 On-Resistance vs. T_J

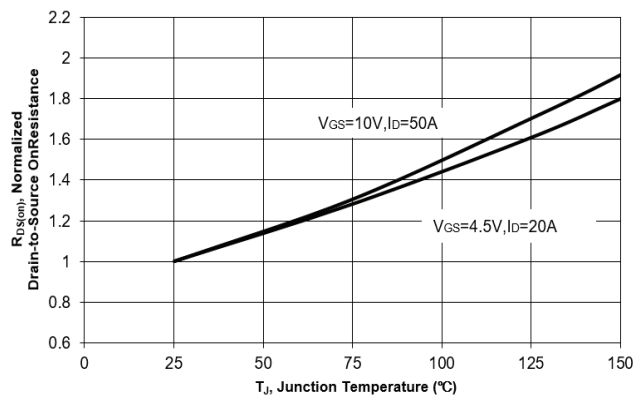
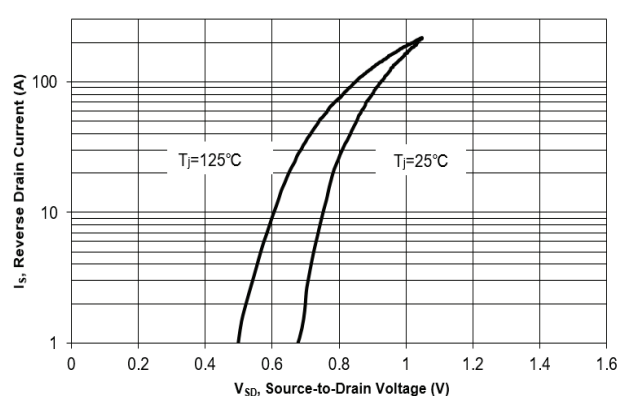


Fig. 6 Typical Body-Diode Forward Characteristics



Electrical Characteristics Curves

Fig. 13 Normalized Maximum Transient Thermal Impedance($Z_{\theta JC}$)

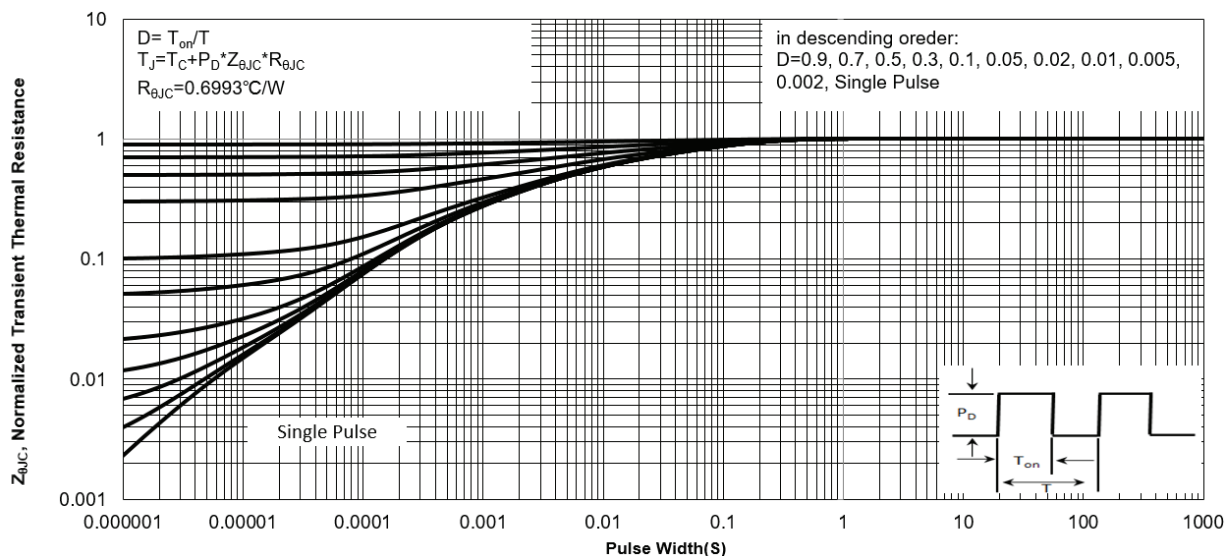


Fig. 14 Normalized Maximum Transient Thermal Impedance($Z_{\theta JA}$)

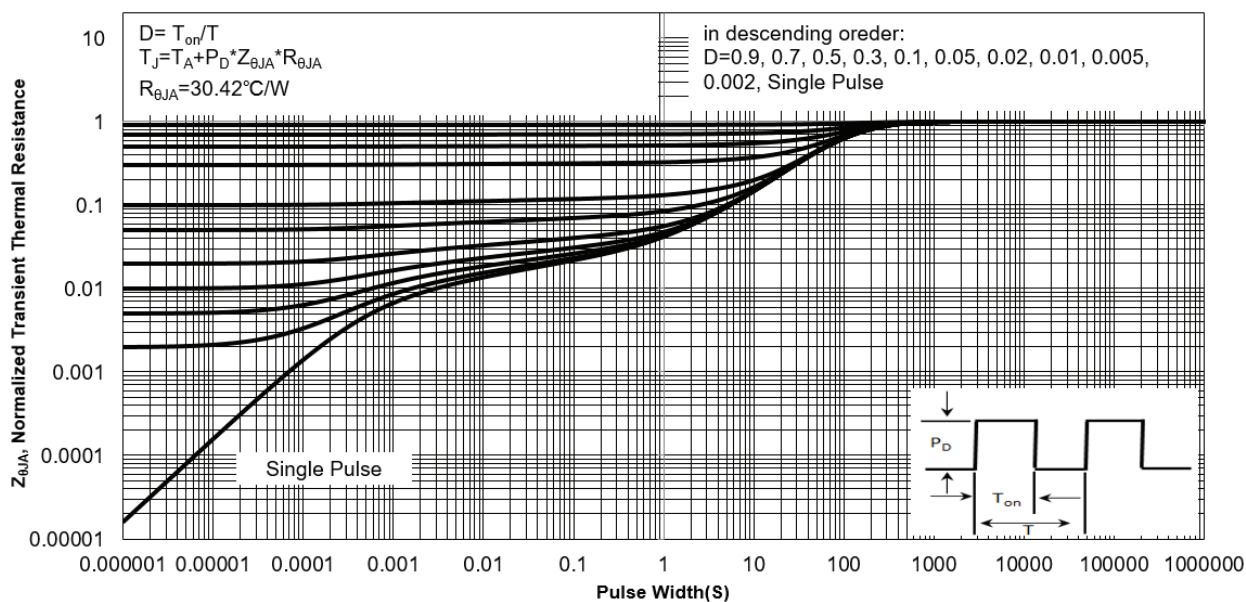


Fig. 7 Typical Junction Capacitance

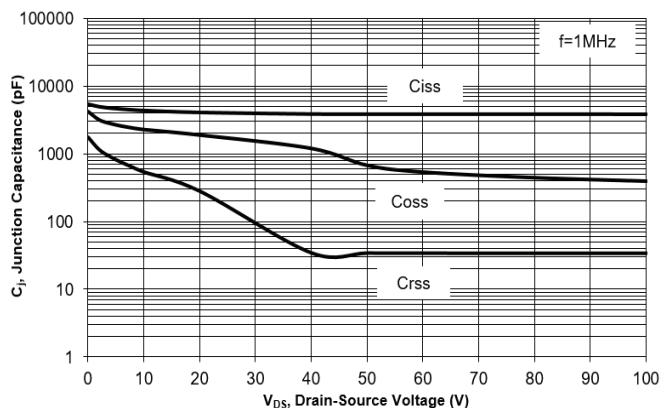


Fig. 8 Drain-Source Leakage Current vs. T_j

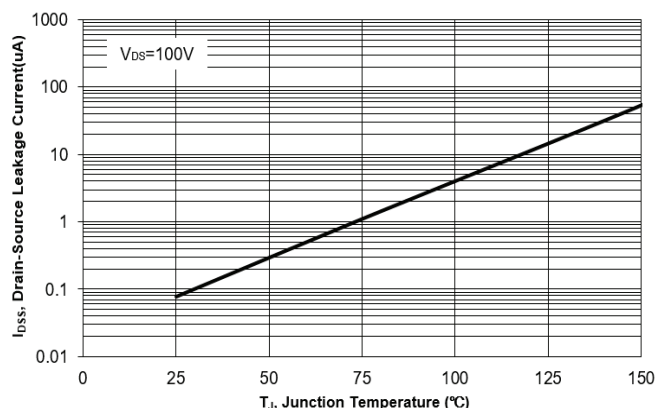


Fig. 9 $V_{(BR)DSS}$ vs. Junction Temperature

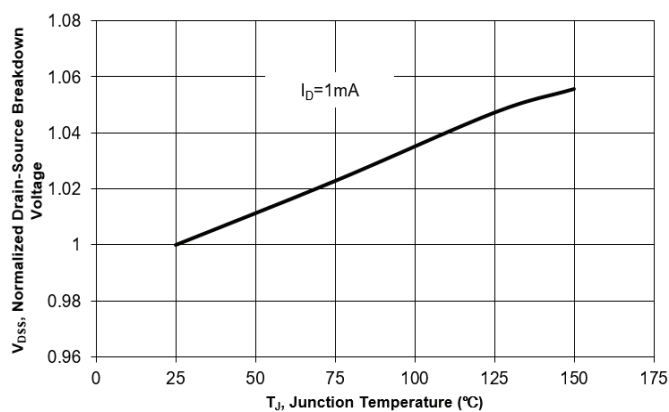


Fig. 10 Gate Threshold Variation vs. T_j

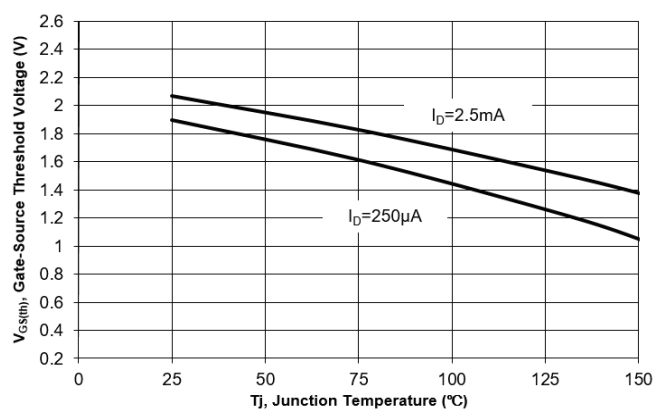


Fig. 11 Gate Charge

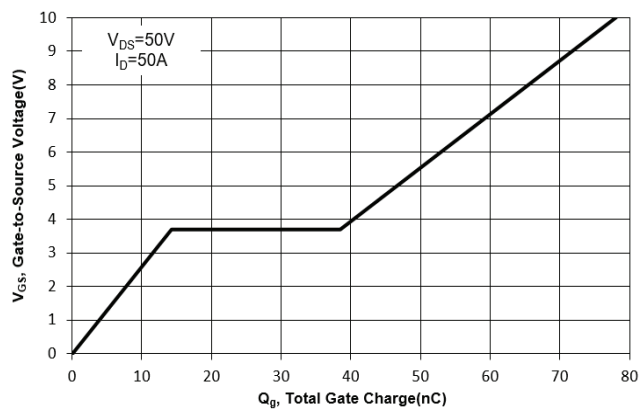
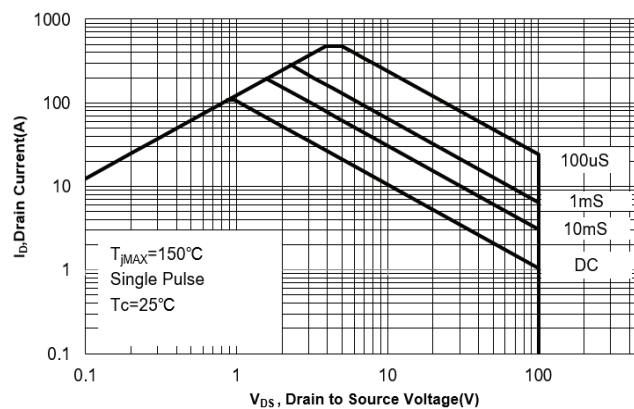


Fig. 12 Safe Operation Area



Test Circuits

Fig.1-1 Switching times test circuit

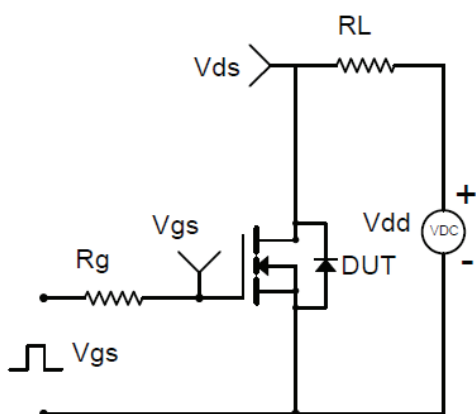


Fig.1-2 Switching Waveform

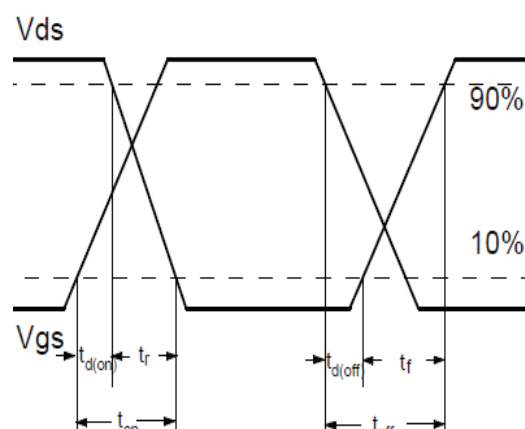


Fig.2-1 Gate charge test circuit

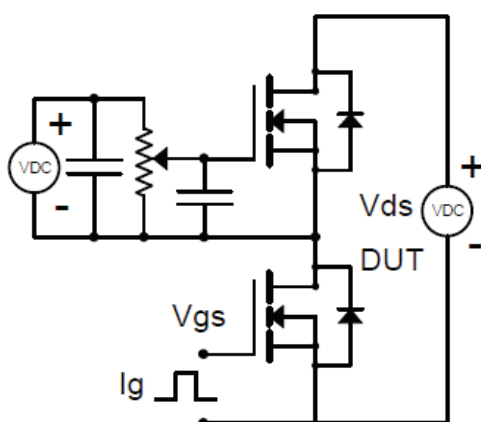


Fig.2-2 Gate charge waveform

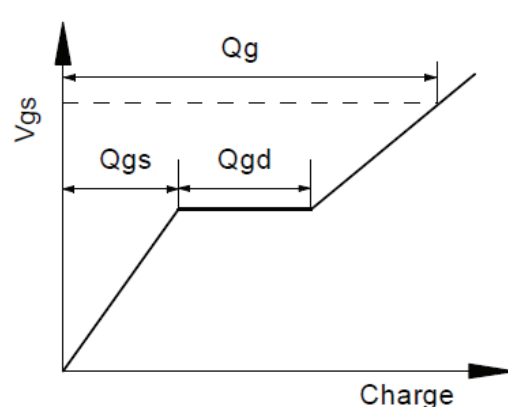


Fig.3-1 Avalanche test circuit

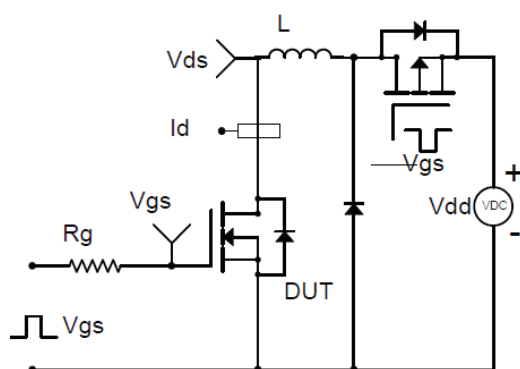
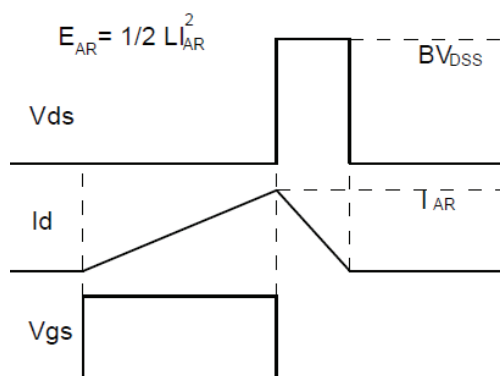
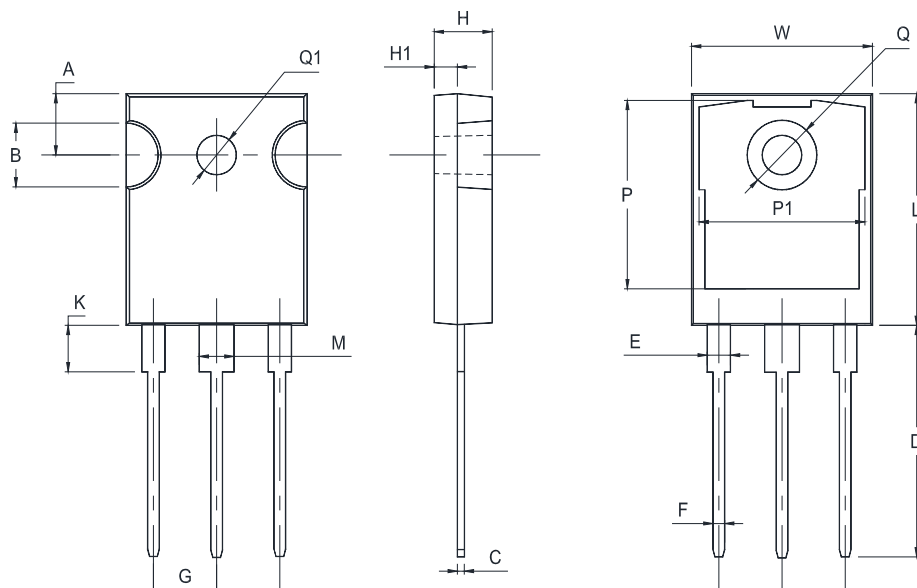


Fig.3-2 Avalanche waveform



Package Outline Dimensions (Units: mm)

TO-247



UNIT	A	B	C	D	E	F	G	W	H	H1	K	L	M	P
mm	6.5	5.2	0.7	20.3	2.2	1.3	5.7	16.2	5.3	2.4	4.45	21.3	3.2	16.6
	5.9	4.6	0.5	19.7	1.8	1.1	5.1	15.8	4.7	1.8	4.05	20.7	2.8	16.2

UNIT	P1	Q	Q1
mm	14.2	7.35	4.2
	13.8	7.05	3.6

Packing information

Package	Carton Quantity	Box Quantity	Base Quantity	Delivery Mode
TO-247	2.88 K / Carton	720 pcs / Box	30 pcs / Tube	Tube

Marking information

" DPT10N042LS " = Part No

" ***** " = Date Code Marking

Font type: Arial



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